

VERSION WITH MARKINGS TO SHOW CHANGES MADE

4. (once amended) The silicon single crystal ingot production method according to claim 2 [or 3], characterized in that, when producing the silicon single crystal ingot, a pulling speed of the silicon single crystal ingot is changed.

5. (once amended) A silicon single crystal wafer, obtained from the silicon single crystal ingot of [any one of claims 2 thorough 4] claim 2, wherein there exists an OSF ring an inner diameter of which is 70% or less of an overall diameter, and in which there exists, surrounding the OSF ring, a defect free zone occupying 50% or more of a total surface area (on one side).

6. (once amended) A silicon single crystal wafer, obtained from the silicon single crystal ingot of [any one of claims 2 thorough 4] claim 2, wherein there exists an OSF ring an inner diameter of which is 50% or less of an overall diameter, and in which there exists, surrounding the OSF ring, a defect free zone occupying 75% or more of a total surface area (on one side).